L Number	Hits	Search Text	DB	Time stamp
-	69	(438/722).CCLS.	USPAT; US-PGPUB;	2004/09/13
-	69	(("438/722").CCLS.) and @ad<=20010613	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/05/21 15:27
_	223162	438/\$.ccls. or 257/\$.ccls. and @ad<=20010113	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 16:06
-	35716	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/14 14:15
_	4864	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'mosfet'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/14 14:12
-	1	(((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'mosfet') and 'group IV metal'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/14
-	16571	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric layer'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/14 14:21
-	61	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric layer') and 'hafnium' and 'lanthanum'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/08/27 16:46
-	104	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'hafnium' and 'lanthanum'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/14 14:25
-	36	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'amorphous oxide'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/14 14:26
_	1	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric') and 'hafnium' and 'lanthanum' and 'amorphous oxides'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/14 14:26
-	224025	438/\$.ccls. or 257/\$.ccls. and @ad<=20010613	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/25 11:50
-	15	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric metal oxide'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/15 10:49
-	4906	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/15

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_	73	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'mosfet' and 'dielectric') and 'hafnium'	USPAT; US-PGPUB; EPO; JPO;	2002/06/25 15:23
			DERWENT; IBM TDB	
-	24	(((438/\$.ccls. or 257/\$.ccls. and	USPAT;	2002/02/15
		<pre>@ad<=20010613) and 'mosfet' and 'dielectric') and 'hafnium') and</pre>	US-PGPUB; EPO; JPO;	10:55
		'lanthanum'	DERWENT;	
_	2	("6020024").PN.	IBM_TDB USPAT;	2002/02/15
	:		US-PGPUB;	11:22
			EPO; JPO; DERWENT;	
	4	(#442202E#\ px	IBM_TDB	2002/02/15
-	4	("4432035").PN.	USPAT; US-PGPUB;	2002/02/15 13:44
			EPO; JPO;	
			DERWENT; IBM TDB	
_	417	(257/411).CCLS.	USPĀT;	2004/04/12
			US-PGPUB; EPO; JPO;	14:07
			DERWENT; IBM TDB	
_	5	(("257/411").CCLS.) and 'hafnium' and	USPAT;	2002/02/15
		'lanthanum'	US-PGPUB; EPO; JPO;	13:46
			DERWENT;	
_	230368	438/\$.ccls. or 257/\$.ccls. and	IBM_TDB USPAT;	2002/06/25
	230300	@ad<=20010613	US-PGPUB;	11:54
			EPO; JPO; DERWENT;	
			IBM_TDB	
_	168	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'hafnium' and	USPAT; US-PGPUB;	2002/12/23
		'lanthanum'	EPO; JPO; DERWENT;	
			IBM_TDB	
_	2	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'hafnium' and	USPAT; US-PGPUB;	2002/06/25
		'combining' with 'oxygen'	EPO; JPO;	
			DERWENT; IBM TDB	
-	91	(438/\$.ccls. or 257/\$.ccls. and	USPAT;	2002/06/25
		@ad<=20010613) and 'hafnium' with 'oxygen'	US-PGPUB; EPO; JPO;	12:07
			DERWENT; IBM TDB	
-	67	'hafnium' with 'reaction' with 'oxygen'	USPAT;	2002/06/25
			US-PGPUB; EPO; JPO;	12:32
			DERWENT;	
_	3	 'hafnium oxide' near 'formation'	IBM_TDB USPAT;	2002/06/25
			US-PGPUB;	12:33
			EPO; JPO; DERWENT;	
_	58	(438/\$.ccls. or 257/\$.ccls. and	IBM_TDB USPAT;	2002/06/25
-	58	@ad<=20010613) and 'silicon oxide' and	US-PGPUB;	15:42
		'hafnium' and 'lanthanum'	EPO; JPO; DERWENT;	
			IBM_TDB	
_	51	(438/\$.ccls. or 257/\$.ccls. and @ad<=20010613) and 'metal' with	USPAT; US-PGPUB;	2002/06/25
		'reduces' with 'silicon oxide'	EPO; JPO;	
			DERWENT; IBM TDB	

_	199	(438/785).ccls. and @ad<=20010613	USPAT; US-PGPUB; EPO; JPO;	2004/04/12 14:07
			DERWENT; IBM TDB	
-	51	((438/785).ccls. and @ad<=20010613) and 'Hf'	USPAT; US-PGPUB;	2002/06/25 14:05
			EPO; JPO; DERWENT;	
_	32	((438/785).ccls. and @ad<=20010613) and 'Hafnium'	IBM_TDB USPAT; US-PGPUB;	2003/05/21 14:07
		nathium	EPO; JPO; DERWENT;	14.07
_	4	("4432035").PN.	IBM_TDB USPAT;	2002/06/25
			US-PGPUB; EPO; JPO;	14:32
			DERWENT; IBM_TDB	
-	1	"2693629".PN.	USPAT	2002/06/25
_	1	"3819990".PN.	USPAT	2002/06/25
_	1	"4062749".PN.	USPAT	2002/06/25
-	1	"4227944".PN.	USPAT	2002/06/25
_	1	"5106827".PN.	USPAT	2002/06/25
_	1	"5106827".PN.	USPAT	2002/06/25
_	1	"5187638".PN	USPAT	2002/06/25
-	1	"5188902".PN.	USPAT USPAT	2002/06/25 15:21 2002/06/25
_	1	"5273927".PN. "6177361".PN.	USPAT	15:22 2002/06/25
	1	"5824590".PN.	USPAT	15:22 2002/06/25
_	1	"5773314".PN.	USPAT	15:22 2002/06/25
_	1	"5572052".PN.	USPAT	15:22 2002/06/25
_	90	((438/\$.ccls. or 257/\$.ccls. and	USPAT;	15:22 2002/06/25
		<pre>@ad<=20010613) and 'mosfet' and 'dielectric') and 'hafnium'</pre>	US-PGPUB; EPO; JPO;	16:05
		,	DERWENT; IBM TDB	i
-	0	<pre>@ad<=20010613 and 'reduces' with 'silicon dioxide to silicon'</pre>	USPĀT; US-PGPUB;	2002/06/25 15:44
			EPO; JPO; DERWENT;	
_	1028	@ad<=20010613 and 'reduces' with 'silicon	IBM_TDB USPAT;	2002/06/25
		dioxide' with 'silicon'	US-PGPUB; EPO; JPO;	15:47
			DERWENT; IBM_TDB	0000/05/05
_	29	@ad<=20010613 and 'reduces' adj 'silicon dioxide' with 'silicon'	USPAT; US-PGPUB;	2002/06/25 16:01
			EPO; JPO; DERWENT;	
-	4	<pre>@ad<=20010613 and 'hafnium' adj 'silicon dioxide'</pre>	IBM_TDB USPAT; US-PGPUB;	2002/06/25 15:55
		diovide	EPO; JPO; DERWENT;	15.55
			IBM TDB	

_	1	@ad<=20010613 and 'hafnium' adj 'silicon oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/06 09:16
			IBM TDB	
-	126214	438/\$.ccls. or 257/\$.ccls. and @ad<=20010113 and 'high dielectric'	USPAT; US-PGPUB; EPO; JPO;	2002/06/25 16:09
			DERWENT; IBM TDB	
-	124737	438/\$.ccls. or 257/\$.ccls. and @ad<=20010113 and 'high dielectric' and 'silicon oxide' and 'hafnium'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 08:52
-	31	<pre>@ad<=20010113 and 'PVD' with 'ion bombardment'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/07/11
			DERWENT;	
_	393	<pre>@ad<=20010113 and 'high dielectric' and 'physical vapor deposition' or 'PVD' with 'ion bombarment'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 09:01
_	393	 @ad<=20010113 and 'high dielectric' and	IBM_TDB USPAT;	2002/07/11
		'physical vapor deposition' or 'PVD' with	US-PGPUB; EPO; JPO;	09:04
		94	DERWENT;	
-	13419	@ad<=20010113 and 'high dielectric	IBM_TDB USPAT; US-PGPUB;	2002/07/11 09:08
		Constant	EPO; JPO; DERWENT; IBM TDB	03.00
-	332	(@ad<=20010113 and 'high dielectric constant') and 'physical vapor deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 09:09
-	0	((@ad<=20010113 and 'high dielectric constant') and 'physical vapor deposition') and 'ion bombardment energy'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11
-	16	((@ad<=20010113 and 'high dielectric constant') and 'physical vapor deposition') and 'ion bombardment'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11
	1	#440F210# DV	IBM_TDB USPAT	2002/07/11
-	1	"4495219".PN.		10:00
-	1	"6013553".PN.	USPAT	2002/07/11 10:00
-	1	"6015739".PN.	USPAT	2002/07/11 10:00
-	1	"5464792".PN.	USPAT	2002/07/11 10:00
-	1	"6020024".PN.	USPAT	2002/07/11 10:01
_	1	"6020243".PN.	USPAT	2002/07/11
-	1	"6060755".PN.	USPAT	2002/07/11
-	1	"6110784".PN.	USPAT	2002/07/11
-	6	@ad<=20010113 and 'hafnium deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11
1			IBM_TDB	1

_	22	<pre>@ad<=20010113 and 'hafnium' and 'PVD' and 'ion bombardment'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 11:52
-	3	<pre>@ad<=20010113 and 'hafnium' and 'PVD' and 'ion bombardment' and 'eV'</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/07/11 11:51
-	3	@ad<=20010113 and 'hafnium' and	DERWENT; IBM_TDB USPAT;	2003/11/06
		'sputtering' and 'ion bombardment' with 'eV'	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	09:10
_	53	<pre>@ad<=20010113 and 'metal' and 'sputtering' and 'ion bombardment' with 'eV'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/11 12:56
-	1	"4520413".PN.	USPAT	2002/07/11 13:08
_	1	"5930611".PN.	USPAT	2002/07/11 13:08
-	1	"6054331".PN.	USPAT	2002/07/11 13:09
_	1	"6060391".PN.	USPAT	2002/07/11 13:11
-	1	"6069070".PN.	USPAT	2002/07/11 13:12
_	266	<pre>@ad<=20010113 and 'hafnium' with 'sputtering'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/11 13:15
-	22	@ad<=20010113 and 'hafnium' and 'PVD' and 'ion bombardment'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/23 12:01
_	22	<pre>@ad<=20010613 and 'hafnium' and 'PVD' and 'ion bombardment'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/23 12:09
-	1	"4173661".PN.	USPAT	2002/07/23 12:08
-	1	"5773363".PN.	USPAT	2002/07/23 12:08
_	5	<pre>@ad<=20010613 and 'hafnium' and 'PVD' and 'ion bombardment' with 'energy'</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/23
_	6	@ad<=20010613 and 'PVD' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/07/23 12:40
-	3	@ad<=20010613 and 'hafnium' and 'ion bombardment' with 'eV'	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:52
_	29	@ad<=20010613 and 'PVD' and 'oxygen radical'	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/07/23 12:38
1			IBM_TDB	

_	67	<pre>@ad<=20010613 and 'sputter' and 'oxygen radical'</pre>	USPAT; US-PGPUB; EPO; JPO;	2002/07/23 12:39
			DERWENT; IBM TDB	
_	19	<pre>@ad<=20010613 and 'hafnium' and 'sputter'</pre>	USPAT;	2002/07/23
		with 'eV'	US-PGPUB;	12:50
			EPO; JPO;	
			DERWENT; IBM TDB	
-	4	•	USPAT;	2002/07/23
		'sputter'and 'oxygen radical' with 'eV'	US-PGPUB;	12:44
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	6	• • • • • • • • • • • • • • • • • • • •	USPAT;	2002/07/23
		with 'eV'	US-PGPUB; EPO; JPO;	12:50
			DERWENT;	
			IBM_TDB	
-	14	<pre>@ad<=20010613 and 'hafnium' and 'ion bombardment' and 'sputter' and 'eV'</pre>	USPAT; US-PGPUB;	2002/07/23
		bombardment and spacter and ev	EPO; JPO;	15.01
			DERWENT;	
_	912	 @ad<=20010613 and 'dielectric deposition'	IBM_TDB USPAT;	2002/07/23
	312	Gad\-20010015 and dielectic deposition	US-PGPUB;	13:10
			EPO; JPO;	
			DERWENT; IBM TDB	
_	118	(@ad<=20010613 and 'dielectric	USPAT;	2002/07/23
i		deposition') and 'refractory metal'	US-PGPUB;	13:09
			EPO; JPO; DERWENT;	
	İ		IBM TDB	
-	1		USPAT;	2002/07/23
		deposition') and 'refractory metal') and 'sputter' and 'eV'	US-PGPUB; EPO; JPO;	13:09
			DERWENT;	
	0	((@ad<=20010613 and 'dielectric	IBM_TDB USPAT;	2002/07/23
		deposition') and 'refractory metal') and	US-PGPUB;	13:09
		'PVD' and 'eV'	EPO; JPO;	
			DERWENT; IBM TDB	
_	12	(@ad<=20010613 and 'dielectric	USPAT;	2002/07/23
		deposition') and 'hafnium'	US-PGPUB;	13:09
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	6	@ad<=20010613 and 'hafnium deposition'	USPAT;	2002/07/23
			US-PGPUB; EPO; JPO;	13.10
			DERWENT;	
_	96	 @ad<=20010613 and 'ion bombardment' with	<pre>IBM_TDB USPAT;</pre>	2002/07/23
	96	'eV'	US-PGPUB;	13:19
			EPO; JPO;	
			DERWENT; IBM TDB	
_	3	(@ad<=20010613 and 'ion bombardment' with	USPAT;	2002/07/23
		'eV') and 'hafnium'	US-PGPUB;	13:20
		·	EPO; JPO; DERWENT;	
			IBM_TDB	
-	2	("6399521").PN.	USPAT;	2002/07/23
			US-PGPUB; EPO; JPO;	14:33
			DERWENT;	
	L		IBM TDB	

		<u> </u>		
_	78	((438/\$.ccls. or 257/\$.ccls. and @ad<=20010113) and 'dielectric layer') and 'hafnium' and 'lanthanum'	USPAT; US-PGPUB;	2002/12/23 12:15
		and narnium and lanthanum	EPO; JPO; DERWENT; IBM TDB	
_	108	((438/\$.ccls. or 257/\$.ccls. and	USPAT;	2002/12/24
		<pre>@ad<=20010113) and 'dielectric layer') and 'hafnium' and 'lanthanum'</pre>	US-PGPUB; EPO; JPO;	08:21
			DERWENT;	
_	8	@ad<=20010113 and 'dielectric layer' and	IBM_TDB USPAT;	2002/12/24
		'hafnium' and 'lanthanum' and 'oxygen'	US-PGPUB;	08:33
		and 'ion bombardment'	EPO; JPO; DERWENT;	
	29	0-d<-20010112 and Inhard and Inhard	IBM_TDB USPAT;	2002/12/24
[-	29	<pre>@ad<=20010113 and 'physical vapor deposition' and 'hafnium' and 'oxygen'</pre>	US-PGPUB;	08:39
		and 'ion bombardment'	EPO; JPO;	
			DERWENT;	
_	62	 @ad<=20010113 and 'dielectric' and	IBM_TDB USPAT;	2002/12/24
		'physical vapor deposition' and 'ion	US-PGPUB;	08:40
		bombardment' same 'energy'	EPO; JPO; DERWENT;	
İ			IBM TDB	
] -	120		USPAT;	2002/12/24
		deposition' and 'ion bombardment' same 'energy'	US-PGPUB; EPO; JPO;	08:40
		energy	DERWENT;	
			IBM_TDB	
-	14	<pre>@ad<=20010113 and 'hafnium' and 'physical vapor deposition' and 'ion bombardment'</pre>	USPAT; US-PGPUB;	2002/12/24
		same 'energy'	EPO; JPO;	
			DERWENT;	
_	2	 @ad<=20010113 and 'lanthanum' and	IBM_TDB USPAT;	2002/12/24
		'physical vapor deposition' and 'ion	US-PGPUB;	08:41
		bombardment' same 'energy'	EPO; JPO; DERWENT;	
			IBM TDB	
-	14		USPAT;	2002/12/24
		deposition' same 'hafnium oxide'	US-PGPUB; EPO; JPO;	08:45
			DERWENT;	
	4	@ad<=20010113 and 'hafnium' and 'electron	IBM_TDB USPAT;	2002/12/24
-	4	beam evaporation' and 'ion bombardment'	USPAT; US-PGPUB;	08:59
		and '10 eV'	EPO; JPO;	
			DERWENT; IBM TDB	
_	3	1 =	USPAT;	2002/12/24
		'electron beam evaporation' and 'ion bombardment' and '10 eV'	US-PGPUB;	09:37
		DOMBALGMENT AND 10 eV	EPO; JPO; DERWENT;	
			IBM_TDB	0000/10/01
-	2	@ad<=20010113 and 'lanthanum' and 'hafnium' and 'oxygen radical'	USPAT; US-PGPUB;	2002/12/24
		naintam and oxygen radical	EPO; JPO;	
			DERWENT;	
_	2	("6387761").PN.	IBM_TDB USPAT;	2003/05/21
			US-PGPUB;	13:36
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	2	("6159855").PN.	USPĀT;	2003/05/21
			US-PGPUB; EPO; JPO;	13:38
			DERWENT;	
			IBM_TDB	

-	2	("6013553").PN.	USPAT;	2003/05/21
			US-PGPUB;	13:38
	1		EPO; JPO;	
	1		DERWENT;	
	0170	0 14 00010610 1 177 6	IBM_TDB	0000/05/05
-	2178	@ad<=20010613 and 'Hafnium' same	USPAT;	2003/05/21
		'Lanthanum'	US-PGPUB;	16:05
			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	1
i -	52	• · · · · · · · · · · · · · · · · · ·	USPAT;	2003/11/06
1		'Hafnium' same 'Lanthanum'	US-PGPUB;	09:17
			EPO; JPO;	
1			DERWENT;	
	20	0 1, 00010610 1, 161 1, 1761	IBM_TDB	0000/05/01
-	39	l 	USPAT;	2003/05/21
		'second' with 'La'	US-PGPUB;	14:42
			EPO; JPO;	
			DERWENT;	
		0-4, 20010(12 15)	IBM_TDB	2002/05/23
-	274	[=	USPAT;	2003/05/21
		and 'second' with 'Group III'	US-PGPUB;	14:45
			EPO; JPO;	
			DERWENT;	
		0 1. 00010610 1.161 1.1 1.5	IBM_TDB	2002/05/22
-	16	I = '	USPAT;	2003/05/21
	1	IVB' and 'second' with 'Group IIIB'	US-PGPUB;	15:06
			EPO; JPO;	j l
			DERWENT;	
		(400 /705)	IBM_TDB	2002/05/24
-	243	(438/785).ccls. and @ad<=20010613	USPAT;	2003/05/21
			US-PGPUB;	15:35
			EPO; JPO;	
ŀ			DERWENT;	
		4400 4000	IBM_TDB	0000/05/01
-	83	(438/722).CCLS. and @ad<=20010613	USPAT;	2003/05/21
			US-PGPUB;	15:31
			EPO; JPO;	1
			DERWENT;	
	455	(057/411) ggrg	IBM_TDB	2002/05/21
_	457	(257/411).CCLS. and @ad<=20010613	USPAT;	2003/05/21
			US-PGPUB;	15:31
			EPO; JPO;	
			DERWENT;	
_	[(257/210) CCTC and Bade-20010612	IBM_TDB USPAT;	2004/04/12
-	59/	(257/310).CCLS. and @ad<=20010613	USPAT; US-PGPUB;	14:08
			EPO; JPO;	13.00
1	1		DERWENT;	
1			IBM TDB	
_	461	(257/410).CCLS. and @ad<=20010613	USPAT;	2004/04/12
	1 401	(201/410).comb. and ead\-20010013	US-PGPUB;	14:08
			EPO; JPO;	13.00
1			DERWENT;	
]	1		IBM TDB	
l _	158	(438/635).CCLS. and @ad<=20010613	USPAT;	2004/04/12
	1 138	(100/000).comb. and Gad-20010010	US-PGPUB;	14:09
	1		EPO; JPO;	
			DERWENT;	
1			IBM TDB	
l _	627	(438/778).CCLS. and @ad<=20010613	USPAT;	2004/04/12
		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	US-PGPUB;	14:10
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	
_	400	(438/758).CCLS. and @ad<=20010613	USPAT;	2004/04/12
		, ,	US-PGPUB;	14:10
	}		EPO; JPO;	
			DERWENT;	1
			IBM TDB	1
	L	<u> </u>		

		 		
-	457	(257/411).CCLS. and @ad<=20010613	USPAT;	2003/05/21
			US-PGPUB; EPO; JPO;	15:36
			DERWENT;	
			IBM TDB	
_	631	(438/240).ccls. and @ad<=20010613	USPAT;	2004/04/12
		(150, 510, 15015; and caa; 50010015	US-PGPUB;	14:11
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	102	(438/216).ccls. and @ad<=20010613	USPAT;	2004/04/12
			US-PGPUB;	14:11
			EPO; JPO;	
			DERWENT;	
	075		IBM_TDB	0004/04/10
-	275	(438/591).ccls. and @ad<=20010613	USPAT;	2004/04/12
			US-PGPUB;	14:12
			EPO; JPO;	
			DERWENT; IBM TDB	
	739	(438/585).ccls. and @ad<=20010613	USPAT;	2004/04/12
_	139	(438/383).CCIS. and Gad<-20010813	US-PGPUB;	14:13
			EPO; JPO;	17.10
			DERWENT;	
			IBM TDB]
_	170	@ad<=20010613 and 'Hafnium oxide' with	USPAT;	2003/11/06
		'Lanthanum oxide'	US-PGPUB;	09:11
	İ		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	"20010013629"	USPĀT;	2003/11/05
			US-PGPUB;	14:41
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	"20020192974"	USPAT;	2003/11/05
			US-PGPUB;	14:41
			EPO; JPO;	
			DERWENT;	
	65	G-d-20010612 and Inilian ovidal with	IBM_TDB USPAT;	2003/11/06
-	65	@ad<=20010613 and 'silicon oxide' with 'Hafnium' with 'Lanthanum'	US-PGPUB;	09:05
		nathium with banthanum	EPO; JPO;	09.05
			DERWENT;	
			IBM TDB	
_	4	(("6159855") or ("6013553")).PN.	USPAT;	2003/11/06
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	09:05
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	3	@ad<=20010113 and 'hafnium' and	USPAT;	2003/11/06
		'sputtering' and 'ion bombardment' with	US-PGPUB;	09:10
		'eV'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	39		USPAT;	2003/11/06
		oxide' with 'Lanthanum oxide'	US-PGPUB;	09:11
			EPO; JPO;	
			DERWENT;	
		0-4-20010612 11-5-2 1 1 1 1	IBM_TDB	2002/11/06
-	2	@ad<=20010613 and 'hafnium' adj 'silicon	USPAT;	2003/11/06 09:16
		oxide'	US-PGPUB;	03:10
İ			EPO; JPO;	
			DERWENT; IBM TDB	
_	58	 @ad<=20010613 and 'dielectric' with	USPAT;	2003/11/06
]	'Hafnium' same 'Lanthanum'	US-PGPUB;	10:12
		Indiana same sancianam	EPO; JPO;	
			DERWENT;	
			IBM TDB	
1	1		1	

-	106	(438/722).CCLS.	USPAT;	2004/04/12
			US-PGPUB;	14:07
			EPO; JPO;	ŀ
			DERWENT;	
			IBM_TDB	
-	593	(257/411).CCLS.	USPAT;	2004/04/12
	1		US-PGPUB;	14:08
			EPO; JPO;	ļ
			DERWENT;	
			IBM_TDB	0004/04/10
-	259	(438/785).ccls. and @ad<=20010613	USPAT;	2004/04/12
İ			US-PGPUB;	14:08
	,		EPO; JPO;	
			DERWENT;	
		(057/010) 6676 1 0 1 00010613	IBM_TDB	0004/04/10
_	629	(257/310).CCLS. and @ad<=20010613	USPAT;	2004/04/12
			US-PGPUB;	14:09
			EPO; JPO;	1.
			DERWENT;	
	400	(257/410) CCTC and Gade-20010C13	IBM_TDB USPAT;	2004/04/12
-	482	(257/410).CCLS. and @ad<=20010613	US-PGPUB;	14:10
			EPO; JPO;	14.10
			DERWENT;	
1			IBM TDB	
	660	(438/778).CCLS. and @ad<=20010613	USPAT;	2004/04/12
-	000	(130///0).CCD3. and edux-20010013	US-PGPUB;	14:11
			EPO; JPO;	1 13.11
			DERWENT;	
			IBM TDB	
1_	434	(438/758).CCLS. and @ad<=20010613	USPAT;	2004/04/12
	434	(450/750).ccm5. and ead<-20010015	US-PGPUB;	14:12
			EPO; JPO;	1 1
į			DERWENT;	
			IBM TDB	
_	114	(438/216).ccls. and @ad<=20010613	USPAT;	2004/04/12
	113	(150/210).ccis. and cad 25015015	US-PGPUB;	14:12
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	287	(438/591).ccls. and @ad<=20010613	USPAT;	2004/04/12
		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	US-PGPUB;	14:13
			EPO; JPO;	1
			DERWENT;	
			IBM_TDB	
_	760	(438/585).ccls. and @ad<=20010613	USPAT;	2004/04/12
			US-PGPUB;	14:14
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	671	(438/240).ccls. and @ad<=20010613	USPAT;	2004/04/12
			US-PGPUB;	14:20
		•	EPO; JPO;	1
			DERWENT;	
	1 44	(/UC704E00U) om /UCC7000CU)	IBM_TDB USPAT;	2004/09/13
-	14	(("6784508") or ("6679996") or ("6348373") or ("6573160") or ("6495474")	USPAT; US-PGPUB;	2004/09/13
		or ("6713846") or ("6407435")).PN.	EPO; JPO;	14.19
		OT (0/13040) OT (040/435)).FN.	DERWENT;	
			IBM TDB	
1_	2	("20020190302").PN.	USPAT;	2004/09/13
-	2	(20020190302	US-PGPUB;	11:09
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	2	("20020106536").PN.	USPAT;	2004/09/13
		,, ,	US-PGPUB;	11:09
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

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-	2	("6573197").PN.	USPAT;	2004/09/13
			US-PGPUB;	12:38
			EPO; JPO;	i
			DERWENT;	
		•	IBM TDB	
-	2	("6184072").PN.	USPĀT;	2004/09/13
			US-PGPUB;	12:38
			EPO; JPO;	1
			DERWENT;	
1			IBM TDB	